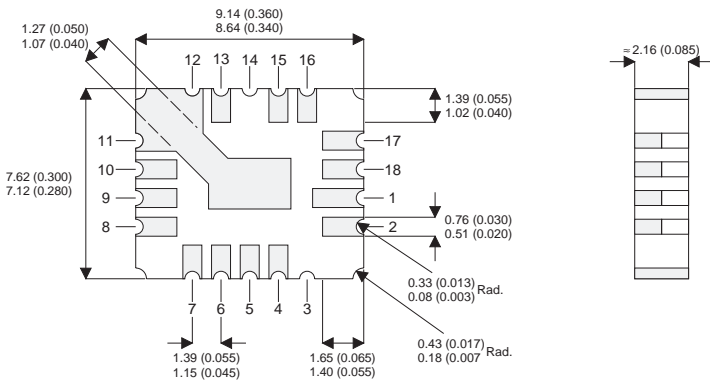


MECHANICAL DATA

Dimensions in mm (inches)

**N-CHANNEL
POWER MOSFET**



V_{DSS} **200V**
 $I_{D(cont)}$ **4.8A**
 $R_{DS(on)}$ **0.46Ω**

FEATURES

- SURFACE MOUNT
- SMALL FOOTPRINT
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- AVALANCHE ENERGY RATING
- SIMPLE DRIVE REQUIREMENTS
- LIGHT WEIGHT

LCC4

MOSFET	TRANSISTOR	PINS
GATE	BASE	4,5
DRAIN	COLLECTOR	1,2,15,16,17,18
SOURCE	EMITTER	6,7,8,9,10,11,12,13

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 10V, T_{case} = 25^{\circ}C$)	4.8A
I_D	Continuous Drain Current ($V_{GS} = 10V, T_{case} = 100^{\circ}C$)	3.1A
I_{DM}	Pulsed Drain Current ¹	19A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	22W
	Linear Derating Factor	0.17W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	54mJ
dv/dt	Peak Diode Recovery ³	4.5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150 $^{\circ}C$
	Surface Temperature (for 5 sec).	300 $^{\circ}C$

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s, \delta \leq 2\%$
- 2) @ $V_{DD} = 50V, L \geq 570\mu H, R_G = 25\Omega, Peak I_L = 14A, Starting T_J = 25^{\circ}C$
- 3) @ $I_{SD} \leq 14A, di/dt \leq 140A/\mu s, V_{DD} \leq BV_{DSS}, T_J \leq 150^{\circ}C, Suggested R_G = 7.5\Omega$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 1mA$	200		V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to $25^{\circ}C$ $I_D = 1mA$		0.25	$V/^{\circ}C$
$R_{DS(on)}$	Static Drain – Source On-State Resistance ¹	$V_{GS} = 10V$ $I_D = 3.1A$		0.40	Ω
		$V_{GS} = 10V$ $I_D = 4.8A$		0.46	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250mA$	2	4	V
g_{fs}	Forward Transconductance ¹	$V_{DS} \geq 15V$ $I_{DS} = 3.1A$	2.5		S (\bar{v})
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$ $V_{DS} = 0.8BV_{DSS}$ $T_J = 125^{\circ}C$		25	μA
				250	
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = 20V$		100	nA
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = -20V$		-100	
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	$V_{GS} = 0$		600	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		250	
C_{riss}	Reverse Transfer Capacitance	$f = 1MHz$		80	
Q_g	Total Gate Charge	$V_{GS} = 10V$	7.4	42.1	nC
Q_{gs}	Gate – Source Charge	$I_D = 4.8A$	2.5	5.3	
Q_{gd}	Gate – Drain (“Miller”) Charge	$V_{DS} = 0.5BV_{DSS}$	6.0	28.1	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100V$ $I_D = 4.8A$ $R_G = 7.5\Omega$		30	ns
t_r	Rise Time			50	
$t_{d(off)}$	Turn-Off Delay Time			50	
t_f	Fall Time			40	
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current			4.8	A
I_{SM}	Pulse Source Current ²			19	
V_{SD}	Diode Forward Voltage ¹	$I_S = 4.8A$ $T_J = 25^{\circ}C$ $V_{GS} = 0$		1.4	V
t_{rr}	Reverse Recovery Time	$I_F = 4.8A$ $T_J = 25^{\circ}C$		6.0	ns
Q_{rr}	Reverse Recovery Charge ¹	$d_i / d_t \leq 100A/\mu s$ $V_{DD} \leq 50V$		3.0	μC
t_{on}	Forward Turn-On Time		Negligible		
PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)		1.8		nH
L_S	Internal Source Inductance (from 6mm down source lead to source bond pad)		4.3		
THERMAL CHARACTERISTICS					
$R_{\theta JC}$	Thermal Resistance Junction – Case			5.8	$^{\circ}C/W$
$R_{\theta JPC}$	Thermal Resistance Junction – PC Board			19	

Notes

- 1) Pulse Test: Pulse Width $\leq 300ms$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.